

Appl. No. 10/829,053
Reply to Office action of 06/17/2005

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method for manufacturing a ferroelectric capacitor, comprising:

forming a first electrode layer;

forming a ferroelectric dielectric layer over the first electrode layer;

planarizing the ferroelectric dielectric layer to form a planarized ferroelectric dielectric layer; and

forming a second electrode layer over the planarized ferroelectric dielectric layer;
and

cleaning the planarized ferroelectric dielectric layer prior to forming the second electrode layer.

2. (original) The method as recited in Claim 1 wherein planarizing the ferroelectric dielectric layer includes planarizing the ferroelectric dielectric layer using a chemical mechanical polishing process until it is substantially planar.

3. (original) The method as recited in Claim 2 wherein the substantially planar ferroelectric dielectric layer has an average surface roughness of less than about 1 nm.

4. (original) The method as recited in Claim 3 wherein the substantially planar ferroelectric dielectric layer has an average surface roughness of less than about 0.5 nm.